

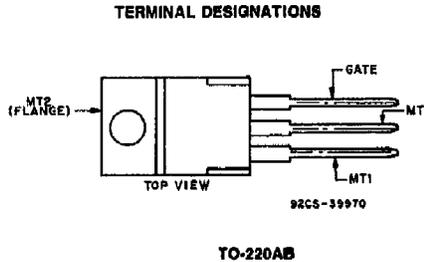
2N6342A-2N6349A Series

12-A Silicon Triacs

For Power Control and Power-Switching Applications

Features:

- 800V, 125 Deg. C T_J Operating
- High dv/dt and di/dt Capability
- Low Switching Losses
- High Pulse Current Capability
- Low Forward and Reverse Leakage
- Silicon Oxide Glass Multilayer Passivation System
- Advanced Unisurface Construction
- Precise Ion Implanted Diffusion Source



The 2N6342A-2N6349A series triacs are gate-controlled full-wave silicon switches utilizing a plastic case with three leads to facilitate mounting on printed-circuit boards. They are intended for the control of ac loads in such applications as motor controls, light dimmers, heating controls, and power-switching systems.

These devices are designed to switch from an off-state to an

on-state for either polarity of applied voltage with positive or negative gate triggering voltages. They have an on-state current rating of 12 amperes at a T_C of 80°C and repetitive off-state voltage ratings of 200, 400, 600, and 800 volts. The plastic package design provides not only ease of mounting but also low thermal impedance, which allows operation at high case temperatures and permits reduced heat-sink size.

MAXIMUM RATINGS, Absolute-Maximum Values:

	2N6342A 2N6346A	2N6343A 2N6347A	2N6344A 2N6348A	2N6345A 2N6349A	
*V _{DRM} * T _J = -40 to 110°C	200	400	600	800	V
†I _{T(RMS)} T _C = 80°C, θ 360°	12				A
For other conditions	See Figs. 5				
‡I _{TSM}					
For one cycle of applied principal voltage					
60 Hz (sinusoidal), T _C = 80°C	120				A
50 Hz (sinusoidal), T _C = 80°C	113				A
For more than one cycle of applied principal voltage	See Fig. 6				
di/dt					
V _D = V _{DRM} , I _{GT} = 200 mA, t _r = 0.1 μs	100				A/μs
I _{rt} (At T _C shown for I _{T(RMS)} , half-sine wave):					
t = 10 ms	64				A ² s
= 2.5 ms	40				A ² s
= 0.5 ms	23				A ² s
= 1 to 8.3 ms	40				A ² s
*I _{GT(M)}					
For 1 μs max.	4				A
*P _{GM} (For 1 μs max., I _{GT(M)} ≤ 4 A)	20				W
*P _{GM}	0.5				W
*T _{stg}	-40 to 150				°C
*T _C	-40 to 110				°C
*T _r During soldering for 10 s max.	230				°C

*In accordance with JEDEC registration data format JC-22 RDF-2.

†For either polarity to main terminal 2 voltage (V_{MT2}) with reference to main terminal 1.

‡For either polarity to gate voltage (V_G) with reference to main terminal 1.



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Quality Semi-Conductors

2N6342A-2N6349A Series

ELECTRICAL CHARACTERISTICS

At Maximum Ratings Unless Otherwise Specified, and at Indicated Temperatures

CHARACTERISTIC	LIMITS			UNITS
	For All Types Except as Specified			
	Min.	Typ.	Max.	
I_{DROM}^{\bullet} $T_J = 110^{\circ}\text{C}$, $V_{DROM} = \text{Max, rated value}$	—	—	2	mA
V_{TM}^{\bullet} $I_T = 17\text{A (peak)}$, $T_C = 25^{\circ}\text{C}$	—	1.3	1.75	V
I_{HO}^{\bullet} Gate open, initial principal current = 200 mA $V_D = 12\text{V}$, $T_C = 25^{\circ}\text{C}$ $= -40^{\circ}\text{C}$	—	6	40 75	mA
dv/dt^{\bullet} (Commutating) $V_D = V_{DROM}$, $I_{TM} = 17\text{A}$, $di/dt = 6.5\text{A/ms}$. $T_C = 80^{\circ}\text{C}$	—	5	—	V/ μs
dv/dt^{\bullet} (Off-State) $V_D = V_{DROM}$, $T_C = 100^{\circ}\text{C}$				
2N6342A, 2N6346A	100	300	—	
2N6343A, 2N6347A	75	250	—	
2N6344A, 2N6348A	60	200	—	
2N6345A, 2N6349A	30	70	—	
I_{GT}^{\bullet} $V_D = 12\text{V (dc)}$, $R_L = 100\ \Omega$				mA
Mode V_{MT2} V_G				
1+ + +	—	—	—	
$T_C = 25^{\circ}\text{C}$ 111- - -	—	6	50	
1- + - (2N6346A-49A only)	—	10	50	
111+ - + (2N6346A-49A only)	—	6	75	
	—	25	75	
$T_C = -40^{\circ}\text{C}$ 1+ + +	—	—	100	
111- - -	—	—	100	
1- + - (2N6346A-49A only)	—	—	125	
111+ - + (2N6346A-49A only)	—	—	125	
V_{GT}^{\bullet} $V_D = 12\text{V (dc)}$, $R_L = 100\ \Omega$				V
Mode V_{MT2} V_G				
1+ + +	—	0.9	2	
$T_C = 25^{\circ}\text{C}$ 111- - -	—	1.1	2	
1- + - (2N6346A-48A only)	—	0.9	2.5	
111+ - + (2N6346A-48A only)	—	1.4	2.5	
1+ + +	—	—	2.5	
$T_C = -40^{\circ}\text{C}$ 111- - -	—	—	2.5	
1- + - (2N6346A-49A only)	—	—	3	
111+ - + (2N6346A-49A only)	—	—	3	
$V_D = V_{DROM}$, $R_L = 10\ \text{K}\ \Omega$				
1+ + +	0.2	—	—	
$T_J = 110^{\circ}\text{C}$ 111- - -	0.2	—	—	
1- + - (2N6346A-49A only)	0.2	—	—	
111+ 1- + (2N6346A-49A only)	0.2	—	—	
t_{gt}^{\bullet} $V_D = V_{DROM}$, $I_{GT} = 120\text{mA}$, $t_r = 0.1\ \mu\text{s}$, $i_T = 17\text{A (peak)}$, $T_C = 25^{\circ}\text{C}$	—	1.5	2	μs
$R_{\theta JC}$	—	—	2	$^{\circ}\text{C/W}$

¹In accordance with JEDEC registration data format JC-22 RDF2.

²For either polarity of main terminal 2 voltage (V_{MT2}) with reference to main terminal 1.

³For either polarity of gate voltage (V_G) with reference to main terminal 1.